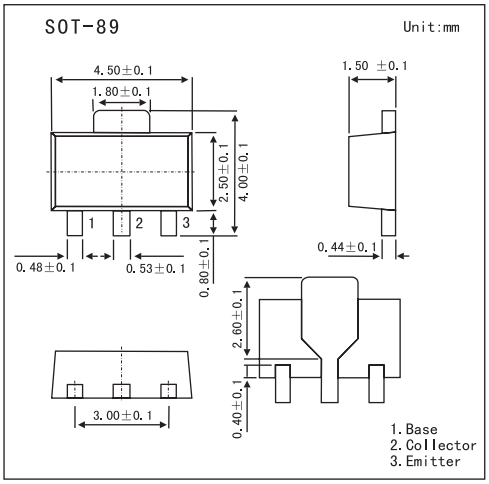
Silicon PNP Epitaxial

2SA1734

■ Features

- Low saturation voltage: $V_{CE(sat)}$ = -0.5 V (max) (I_C = -700 mA).
- High speed switching time: tstg = 0.2μs (typ.).
- Small flat package.
- PC = 1.0 to 2.0 W (mounted on ceramic substrate).



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-40	V
Collector-emitter voltage	V_{CEO}	-30	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-2	A
Base current	I_B	-1.2	A
Collector power dissipation	P_C	500	mW
	P_C *	1000	
Junction temperature	Tj	150	℃
Storage temperature range	T_{stg}	-55 to +150	℃

* Mounted on ceramic substrate (250 mm^2 X 0.8 t)

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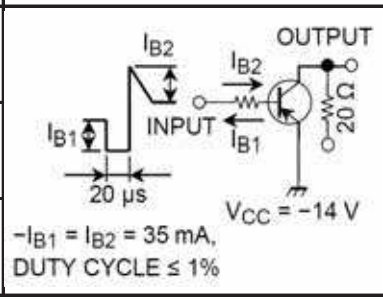
■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = -40 V, I_E = 0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = -6 V, I_C = 0			-0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -10 mA, I_B = 0	-50			V
DC current gain	h_{FE}	V_{CE} = -2 V, I_C =-100 mA	120		400	
		V_{CE} = -2 V, I_C = -1.0A	40			
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = -700 mA, I_B = -35 mA			-0.5	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C = -700 mA, I_B = -35 mA			-1.2	V
Transition frequency	f_T	V_{CE} = -2 V, I_C = -100 mA		100		MHz
Collector output capacitance	C_{ob}	V_{CB} = -10 V, I_E = 0, f = 1 MHz		16		pF
Turn-on time	t_{on}	 $-I_{B1} = I_{B2}$ = 35 mA, DUTY CYCLE ≤ 1%		0.1		μs
Storage time	t_{stg}			0.2		μs
Fall time	t_f			0.1		μs

■ Marking

Marking	LB